

Product features

High precision machining technology
Low temperature drift, high power.
Ceramic substrate, 50 Ω coplanar waveguide
Gold wire bonding

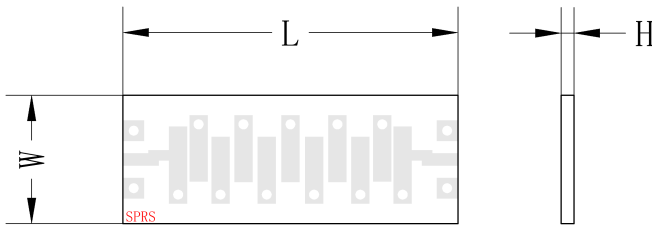
Tech specifications

Items	Parameters	Units
Center Frequency	9.2	GHz
Bandwidth	8.4-10.0	GHz
Center loss	2.3	dB
Ripple	1.0	dB
VSWR	1.7:1	
Group delay ripple	0.5	ns
Rejection	30@DC-7.5GHz	dBc
Rejection	40@11.4-19.0GHz	dBc

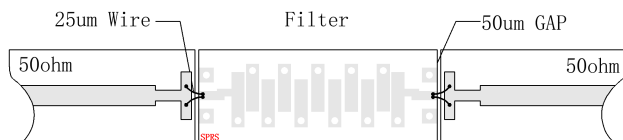
Other requirement (Design assurance)

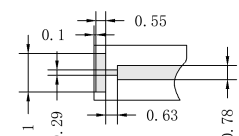
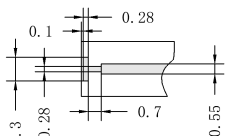
power	2W CW
Work Temp.	-55~+85°C
Storage Temp.	-55~+125°C
Outline size	L:7.5, W:4.5, h:0.26

Outline drawing: Port centered



Suggested PCB Layout

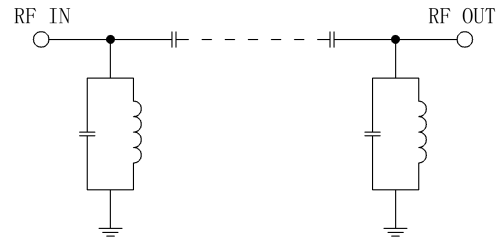


PCB Rogers5880, h: 0.254mm	PCB Rogers4350B, h: 0.254mm
	

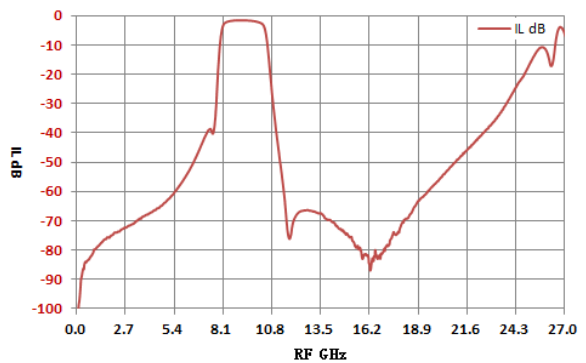
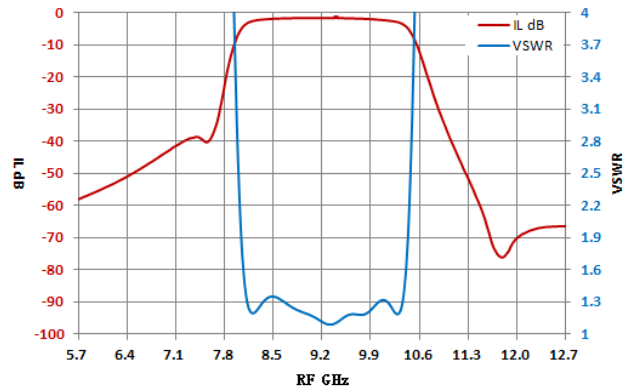
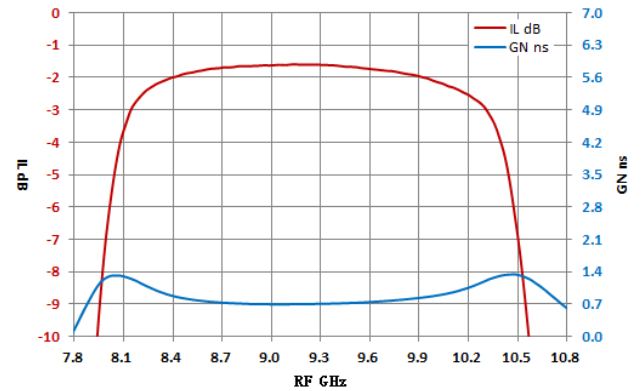
Note

- 0.1mm from the side wall, 2.75mm from the surface to the upper cover.
- Suggest using conductive adhesive for bonding;
- The chip should be installed on kovar alloy or molybdenum copper;
- Suggest using a T-shaped structure for microstrip bonding.

Schematic diagram



Typical test curve



Note: The specifications and performance data contained in this data sheet are based on tests established by COMW.